

AL422 Data Sheets



AL422 3M-Bits FIFO Field Memory

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1.0 Description

The AL422 consists of 3M-bits of DRAM, and is configured as 393,216 words x 8 bit FIFO (first in first out). The interface is very user-friendly since all complicated DRAM operations are already managed by the internal DRAM controller.

Current sources of similar memory (field memory) in the market provide limited memory size which is only enough for holding one TV field, but not enough to hold a whole PC video frame which normally contains 640x480 or 720x480 bytes. The AverLogic AL422 provides 50% more memory to support high resolution for digital PC graphics or video applications. The 50% increase in speed also expands the range of applications.

2.0 Features

- 384K (393,216) x 8 bits FIFO organization
- Support VGA, CCIR, NTSC, PAL and HDTV resolutions
- Independent read/write operations (different I/O data rates acceptable)
- High speed asynchronous serial access
- Read/write cycle time: 20ns
- Access time: 15ns
- Input enable control (write mask)
- Output enable control (data skipping)
- Self refresh
- 5V or 3.3V power supply
- Standard 28-pin SOP package

3.0 Applications

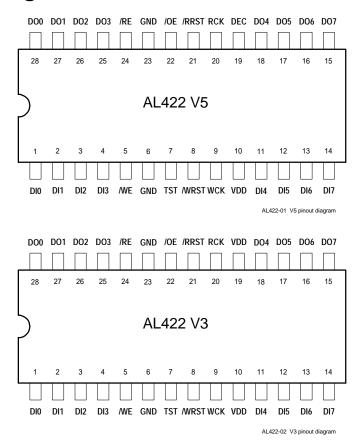
- Multimedia systems
- Video capture systems
- Video editing systems
- Scan rate converters
- TV's picture in picture feature
- Time base correction (TBC)
- Frame synchronizer
- Digital video camera
- Buffer for communications systems

4.0 Ordering Information

Part number	Package	Power Supply
AL422V5	28-pin plastic SOP	+5 volt
AL422V3	28-pin plastic SOP	+3.3 volt



5.0 Pinout Diagram



6.0 Pin Description

Pin name	Pin #	I/O type	Function
DI0~DI7	1~4, 11~14	input	Data input
WCK	9	Input	Write clock
/WE	5	Input (active low)	Write enable
/WRST	8	Input (active low)	Write reset
DO0~DO7	15~18, 25~28	Output (tristate)	Data output
RCK	20	Input	Read clock
/RE	24	Input (active low)	Read enable
/RRST	21	Input (active low)	Read reset
/OE	22	Input (active low)	Output enable
TST	7	Input	Test pin (pulled-down)
VDD	10		5V or 3.3V
DEC/VDD	19		Decoupling cap input
GND	6, 23		Ground



7.0 Electrical Characteristics

7.1 Absolute Maximum Ratings

Parameter		Rat	Unit	
		AL422V3	AL422V5	Omt
V_{DD}	Supply Voltage	-1.0 ~ +4.5	-1.0 ~ +7.0	V
V_P	Pin Voltage	-1.0 ~ +5.5	$-1.0 \sim V_{DD} + 0.5$	V
I_{O}	Output Current	-20 ~ +20	-20 ~ +20	mA
T _{AMB}	Ambient Op. Temperature	0 ~ +70	0 ~ +70	°C
T_{stg}	Storage temperature	-55 ~ +125	-55 ~ +125	°C

7.2 Recommended Operating Conditions

Parameter		AL422V3		AL	Unit	
		Min	Max	Min	Max	Omt
$V_{\scriptscriptstyle DD}$	Supply Voltage	+3.0	+3.6	+4.75	+5.25	V
V_{IH}	High Level Input Voltage	+2.0	+5.5	+2.4	VDD+0.5	V
$V_{\rm IL}$	Low Level Input Voltage	-1.0	+0.8	-1.0	+0.8	V

7.3 DC Characteristics

(VDD=5V for AL422V5, 3.3V for AL422V3, Vss=0V. Ta = 0 to 70°C)

Parameter		AL422V3			AL422V5			Unit
	raiametei		Тур	Max	Min	Тур	Max	Oilit
I_{DD}	Operating Current @20MHz	-	42	-	-	64	-	mA
I_{DD}	Operating Current @50MHz	-	84	-	-	114	-	mA
I_{DDS}	Standby Current	-	20	-	-	20	-	mA
V_{OH}	Hi-level Output Voltage	+2.4	-	VDD	+2.4	-	VDD	V
V_{OL}	Lo-level Output Voltage	-	-	+0.4	-	-	+0.4	V
I_{LI}	Input Leakage Current	-10	-	+10	-10	-	+10	μΑ
I_{LO}	Output Leakage Current	-10	-	+10	-10	-	+10	μΑ



7.4 AC Characteristics

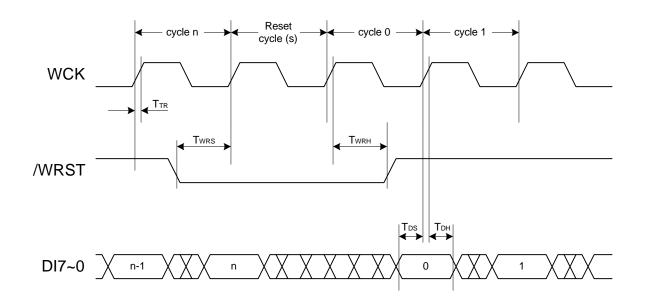
(VDD=5V for AL422V5, 3.3V for AL422V3, Vss=0V, T_{AMB} = 0 to 70°C)

Parameter		AL4	22V3	AL422V5		TT :
	Parameter	Min	Max	Min	Max	Unit
T_{wc}	WCK Cycle Time	20	1000	20	1000	ns
$T_{\scriptscriptstyle WPH}$	WCK High Pulse Width	7	-	7	-	ns
$T_{\scriptscriptstyle WPL}$	WCK Low Pulse Width	7	-	7	-	ns
$T_{\scriptscriptstyle RC}$	RCK Cycle Time	20	1000	20	1000	ns
$T_{\scriptscriptstyle \text{RPH}}$	RCK High Pulse Width	7	-	7	-	ns
$T_{\tiny{\text{RPL}}}$	RCK Low Pulse Width	7	-	7	-	ns
$T_{\scriptscriptstyle AC}$	Access Time	-	15	-	15	ns
Тон	Output Hold Time	3	-	3	-	ns
$T_{\scriptscriptstyle HZ}$	Output High-Z Setup Time	3	15	3	15	ns
$T_{\scriptscriptstyle LZ}$	Output Low-Z Setup Time	3	15	3	15	ns
$T_{\scriptscriptstyle WRS}$	/WRST Setup Time	5	-	5	-	ns
$T_{\scriptscriptstyle WRH}$	/WRST Hold Time	2	-	2	-	ns
$T_{\scriptscriptstyle RRS}$	/RRST Setup Time	5	-	5	-	ns
$T_{\scriptscriptstyle RRH}$	/RRST Hold Time	2	-	2	-	ns
$T_{\scriptscriptstyle DS}$	Input Data Setup Time	5	-	5	-	ns
$T_{\scriptscriptstyle DH}$	Input Data Hold Time	2	-	2	-	ns
$T_{\text{\tiny WES}}$	/WE Setup Time	5	-	5	-	ns
$T_{\scriptscriptstyle WEH}$	/WE Hold Time	2	-	2	-	ns
$T_{\scriptscriptstyle WPW}$	/WE Pulse Width	10	-	10	-	ns
$T_{\scriptscriptstyle RES}$	/RE Setup Time	5	-	5	-	ns
$T_{\scriptscriptstyle \sf REH}$	/RE Hold Time	2	-	2	-	ns
$T_{\scriptscriptstyle RPW}$	/RE Pulse Width	10	-	10	-	ns
$T_{\scriptscriptstyle OES}$	/OE Setup Time	5	-	5	-	ns
Тоен	/OE Hold Time	2	-	2	-	ns
T_{OPW}	/OE Pulse Width	10	-	10	-	ns
$T_{\scriptscriptstyle TR}$	Transition Time	2	20	2	20	ns

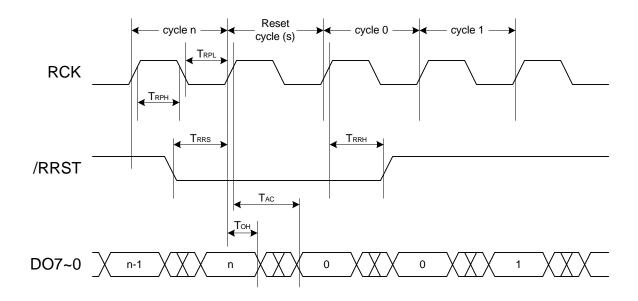
- Input voltage levels are defined as VIH=2.4V and VIL=0.4V.
- The read address needs to be at least 128 cycles after the write address.



7.5 Timing Diagrams

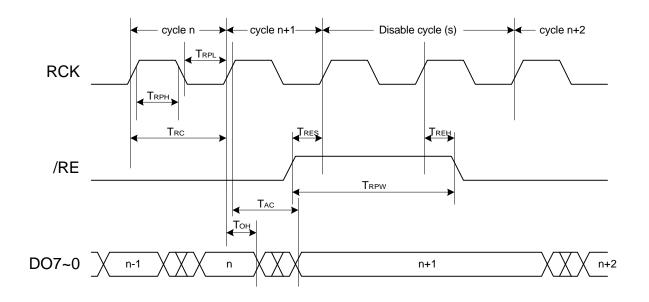


AL422-05 Write Cycle Timing (Write Reset)

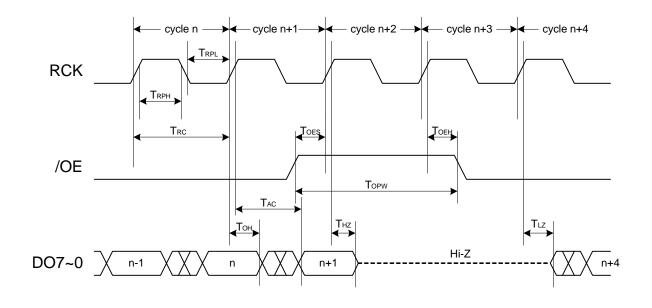


AL422-07 Read Cycle Timing (Read Reset)



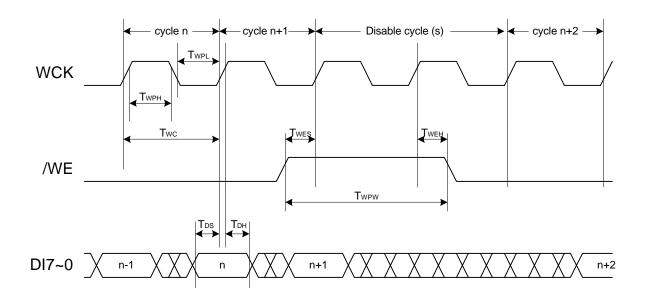


AL422-08 Read Cycle Timing (Read Enable)

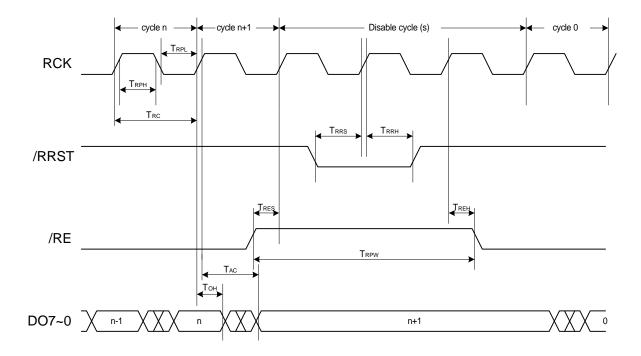


AL422-09 Read Cycle Timing (Output Enable)



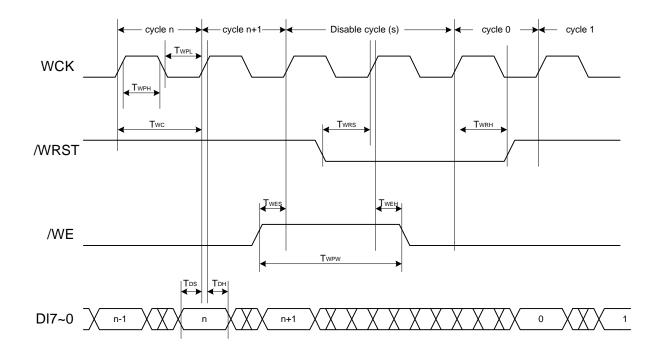


AL422-06 Write Cycle Timing (Write Enable)



AL422-14 Read Cycle Timing (RE, RRST)



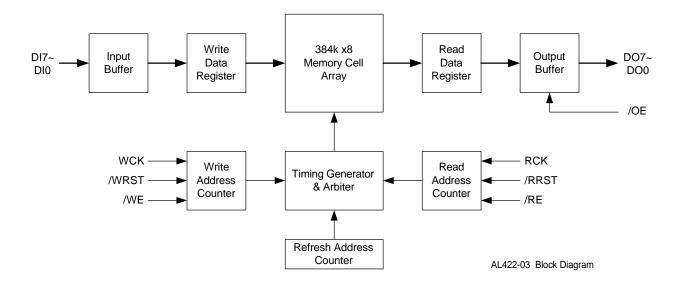


AL422-15 Write Cycle Timing (WE, WRST)



8.0 Functional Description

The AL422 is a video frame buffer consisting of DRAM that works like a FIFO which is long enough to hold up to 819x480 bytes of picture information and fast enough to operate at 50MHz. The functional block diagram is as follows:



The I/O pinouts and functions are described as follows:

DI7~DI0 Data Input: Data is input on the rising edge of the cycle of WCK when /WE is pulled low (enabled).

DO7~DO0 Data Output: Data output is synchronized with the RCK clock. Data is obtained at the rising edge of the RCK clock when /RE is pulled low. The access time is defined from the rising edge of the RCK cycle.

WCK Write Clock Input: The write data input is synchronized with this clock. Write data is input at the rising edge of the WCK cycle when /WE is pulled low (enabled). The internal write address pointer is incremented automatically with this clock input.

RCK Read Clock Input: The read data output is synchronized with this clock. Read data output at the rising edge of the RCK cycle when /OE is pulled low (enabled). The internal read address pointer is incremented with this clock input.

/WE Write Enable Input: /WE controls the enabling/disabling of the data input. When /WE is pulled low, input data is acquired at the rising edge of the WCK cycle. When /WE is pulled high, the memory does not accept data input. The write address pointer is stopped at the current position. /WE signal is fetched at the rising edge of the WCK cycle.



/RE Read Enable Input: /RE controls the operation of the data output. When /RE is pulled low, output data is provided at the rising edge of the RCK cycle and the internal read address is incremented automatically. /RE signal is fetched at the rising edge of the RCK cycle.

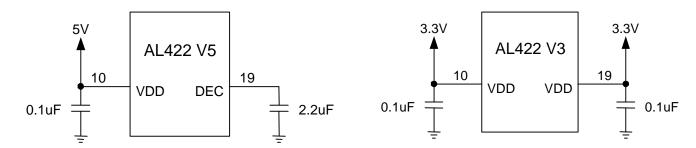
/OE Output Enable Input: /OE controls the enabling/disabling of the data output. When /OE is pulled low, output data is provided at the rising edge of the RCK cycle. When /OE is pulled high, data output is disabled and the output pins remain at high impedance status. /OE signal is fetched at the rising edge of RCK cycle.

/WRST Write Reset Input: This reset signal initializes the write address to 0, and is fetched at the rising edge of the WCK input cycle.

/RRST Write Reset Input: This reset signal initializes the read address to 0, and is fetched at the rising edge of the RCK input cycle.

TST Test Pin: For testing purpose only. It should be pulled low for normal applications.

DEC: Decoupling cap pin, should be connected to a $1\mu F$ or $2.2\mu F$ capacitor to ground. The suggested decoupling circuits for AL422V5 and AL422V3 are as follows respectively:



8.1 Memory Operation

Initialization

Apply /WRST and /RRST 0.1ms after power on, then follow the following instructions for normal operation.

Reset Operation

The reset signal can be given at any time regardless of the /WE, /RE and /OE status, however, they still need to meet the setup time and hold time requirements with reference to the clock input. When the reset signal is provided during disabled cycles, the reset operation is not executed until cycles are enabled again. After WRST and RRST signals are pulled low, the data output and input start from address 0.



Write Operation

Data input DI7~DI0 is written into the write register at the WCK input when /WE is pulled low. The write data should meet the setup time and hold time requirements with reference to the WCK input cycle.

Write operation is prohibited when /WE is pulled high, and the write address pointer is stopped at the current position. The write address starts from there when the /WE is pulled low again. The /WE signal needs to meet the setup time and hold time requirements with reference to the WCK input cycle.

Read Operation

Data output DO7~DO0 is written into the read register at the RCK input when both /RE and /OE are pulled low. The output data is ready after $T_{\scriptscriptstyle AC}$ (access time) from the rising edge of the RCK input cycle.

The read address pointer is stopped at the current position when /RE is pulled high, and starts there when /RE is pulled low again.

/OE needs to be pulled low for read operations. When /OE is pulled high, the data outputs will be at high impedance stage. The read address pointer still increases synchronously with RCK regardless of the /OE status. The /RE and /OE signals need to meet the setup time and hold time requirements with reference to the RCK input cycle.

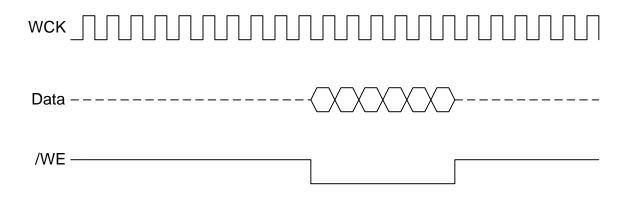
When the new data is read, the read address should be between 128 to 393,247 cycles after the write address, otherwise the output may not be new data.

8.2 Restrictions

Slow Write/Fast Read (or vice versa)

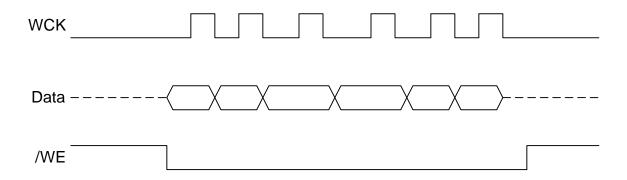
It is recommended that the WCK and RCK are kept running at least 1MHz at all times. Irregular WCK or RCK should be avoided. In case write frequency is much slower than read frequency (or vice versa), keep using a WCK of higher frequency to ensure normal operation and use /WEN to control the write frequency as follows:





AL422-17 Slow Write - Correct

The following drawing shows irregular clock and should be avoided:



AL422-16 Slow Write - Incorrect

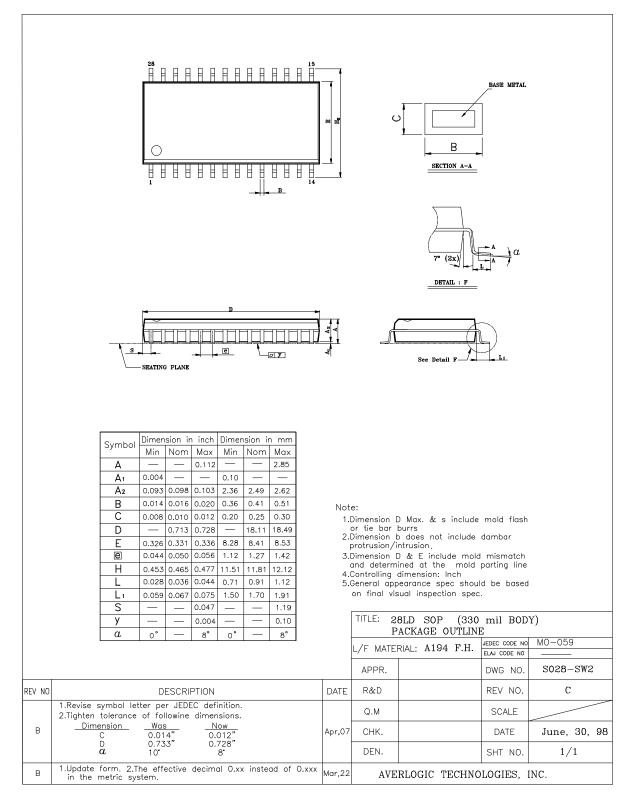
Read Enable during Reset Cycles

It is suggested not to disable /RE during /RRST reset cycles.



9.0 Mechanical Drawing

28 PIN PLASTIC SOP:



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